## INFORMATION DISCLOSURE CITATION

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Applicants	Takashi YODA et al.		
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U.S. PATENT DOCUMENTS						
Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate
pc	2003-0116854-A1	06/26/03	ITO et al.	257	761	
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8	2002-110789	04/12/02	JAPAN			ABSTRACT
PC	2002-176054	06/21/02	JAPAN		<del></del>	ABSTRACT
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	PC	LIN, J. C. et al., "CVD Barriers for Cu with Nanoporous Ultra Low-k: Integration and Reliability", International Interconnect Technology Conference, pp. 21-23, (2002).		
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Examiner	PHAT X. CAO	Date Considered	1/5/04			
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